CLEAN VERSION OF CLAIMS

1. A semiconductor device comprising:

a conductive member;

a cobalt including layer having oxidation resistive and fluorinated acid resistive properties formed over said conductive member; and

a clad layer formed over the cobalt including layer for cladding said cobalt including layer.

2. The semiconductor device as cited in Claim 1, wherein said cobalt including layer is comprised of a cobalt tungsten phosphor layer.

3. The semiconductor device as cited in Claim 1, wherein said clad layer is comprised of a cobalt silicide layer.

4. The semiconductor device as cited in Claim 1, wherein said cobalt including layer [being] is formed on a copper wiring.

5. A method for manufacturing a semiconductor device comprising the steps of:

forming a cobalt including layer on a conductive member; and

forming a cobalt silicide layer on a surface of the cobalt including layer.

6. The method as cited in claim 5, wherein said cobalt silicide layer is formed by exposing said cobalt including layer in a silane system gas.

8. A semiconductor device comprising:

a conductive member;

a layer of CoWP formed over the conductive member; and

a layer of cobalt silicide formed over the layer of CoWP.

9. The semiconductor device of claim 8, wherein the conductive member is a copper wiring.

10. The method of claim 5, wherein the cobalt including layer is a layer comprised of CoWP.

11. The method of claim 5, wherein the conductor is a copper wiring.